

EAST - [10747680.wsp:1]

File View Edit Tools Window Help

Drafts
BRS:
Pending
Active
L1: (3085) semiconductor and spacers\$1 and protective near layer
L2: (6741) spacers\$1 and protective near layer
L4: (58) 2 and ((spacers\$1 with (vertical near sidewall)) or (vertical near spacers\$1) or (rectangu...
L6: (77) 2 and ((spacers\$1 with (vertical near sidewall)) or (vertical near spacers\$1) or (rectangu...
L7: (49518) semiconductor and spacers\$1
L8: (450) 7 and (vertical near spacers\$1 rectangular near spacers\$1 I-shape near spacers\$1 I near sh...
L9: (1) ("6440875").PN.
L10: (2) ("0625764").PN.
L11: (1) ("6625764").PN.
L12: (1) ("6323519").PN.
L3: (12) 2 and (spacers\$1 with (vertical near sidewall))
L5: (58) 2 and ((spacers\$1 with (vertical near sidewall)) or (vertical near spacers\$1) or (rectangu...
L13: (1) ("20050146059")
Failed
2 and ((spacers\$1 with (vertical near sidewall)) or (vertical near spacers\$1 (rectangular near shap...
2 and ((spacers\$1 with (vertical near sidewall)) or (vertical near spacers\$1) or (rectangular near s...
Saved
Favorites
Tagged (0)
UDC
Queue
Trash

Search List Browse Queue Clear
DBs US-PGPUB: USPAT: USOCR: Plurals
Default operator: OR Highlight all hit terms initially
7 and (vertical near spacers\$1 rectangular near spacers\$1
I-shape near spacers\$1 I near shape near spacers\$1 rectangular
near shape near spacers\$1)

BRS form IS&R form Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050146059 A1	20050707	7	Method for forming rectangular-shaped spacers for semiconductor devices		257/900
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20050139933 A1	20050630	10	Semiconductor devices and methods for fabricating the same	257/370	438/234
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20050136676 A1	20050623	13	Method of forming a floating gate for a split-gate flash memory device	438/703	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20050124104 A1	20050609	25	Methods of fabricating semiconductor device having T-shaped gate and L-shaped spacer	438/197	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20050122464 A1	20050609	6	One-drop fill spacerless process for liquid crystal cell on a silicon backplane or microdisplays	349/190	349/156
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20050116293 A1	20050602	34	Transistor structure, memory cell, DRAM, and method for fabricating a transistor structure in a semiconductor substrate	257/349	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20050098820 A1	20050512	13	Method to remove an oxide seam along gate stack edge, when nitride space formation begins with an oxide liner surrounding gate stack	257/314	257/316; 257/E21.682; 257/E27.103;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20050085064 A1	20050421	30	Sacrificial metal spacer damascene process	438/622	257/E21.579
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20050082963 A1	20050421	268	Image formation apparatus	313/493	313/310
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20050067620 A1	20050331	8	Three dimensional CMOS integrated circuits having device layers built on different crystal oriented wafers	257/67	257/74; 257/E27.026; 257/E27.112
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20050064635 A1	20050324	11	METHOD FOR AVOIDING OXIDE UNDERCUT DURING PRE-SILICIDE CLEAN FOR THIN SPACER FETs	438/184	